

**Silicon NPN Power Transistors**

**2SC2555**

**DESCRIPTION**

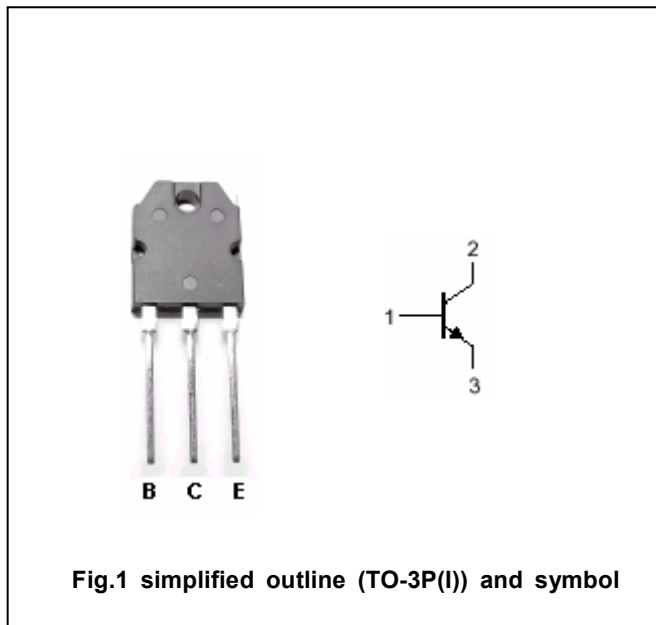
- With TO-3P(I) package
- High collector breakdown voltage  
 $V_{CEO}=400V(\text{Min})$
- Excellent switching times  
 $t_r=1.0\mu s(\text{Max.})$   $t_f=1.0\mu s(\text{Max.})@ I_C=4A$

**APPLICATIONS**

- Switching regulator and high voltage switching applications
- High speed DC-DC converter applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	500	V
$V_{CEO}$	Collector-emitter voltage	Open base	400	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current-DC		8	A
$I_{CM}$	Collector current-peak		10	A
$I_B$	Base current		4	A
$P_C$	Collector power dissipation	$T_a=25^\circ C$	2.5	W
		$T_C=25^\circ C$	80	
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	400			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA, I <sub>E</sub> =0	500			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.8A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.8A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =400V; I <sub>E</sub> =0			100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			1.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	15			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =4A; V <sub>CE</sub> =5V	10			

## Switching times

t <sub>r</sub>	Rise time	V <sub>CC</sub> ≈200V; R <sub>L</sub> =50Ω I <sub>B1</sub> =-I <sub>B2</sub> =0.4A			1.0	μs
t <sub>stg</sub>	Storage time				2.5	μs
t <sub>f</sub>	Fall time				1.0	μs

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PACKAGE OUTLINE

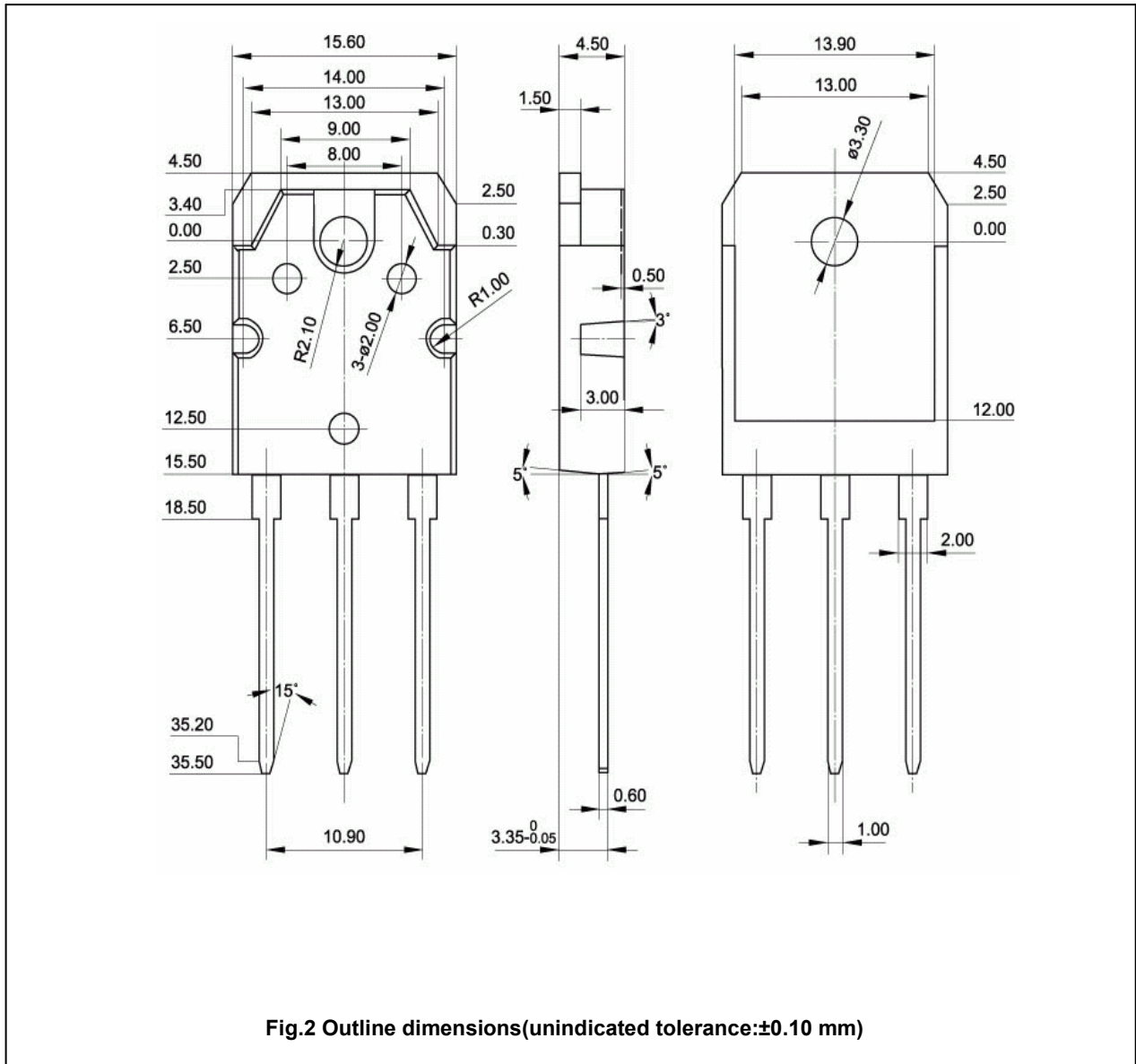


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)

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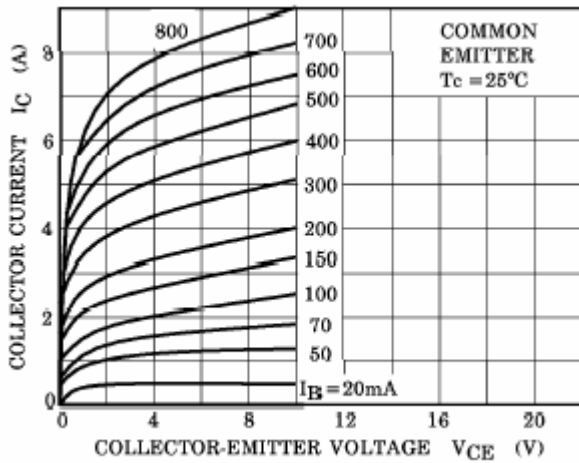


Fig.3 Static Characteristic

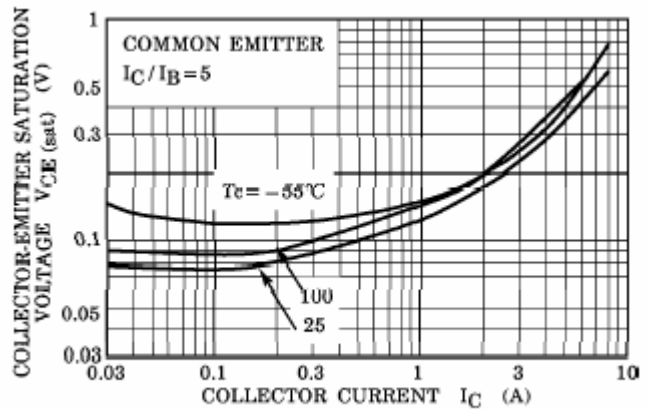


Fig.4 Collector-Emitter Saturation Voltage

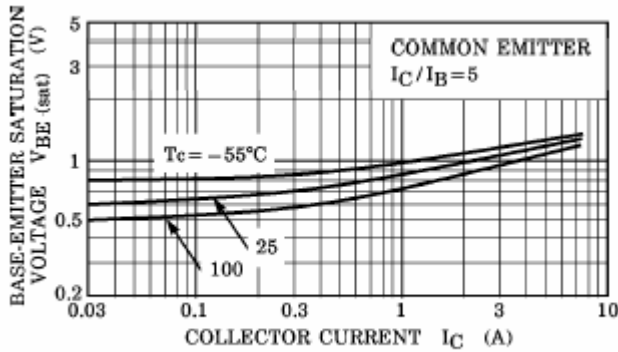


Fig.5 Base-Emitter Saturation Voltage

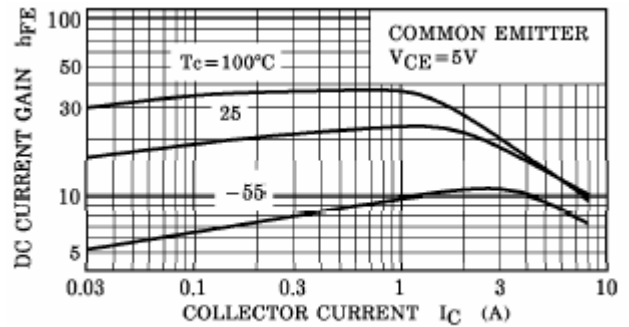


Fig.6 DC current Gain

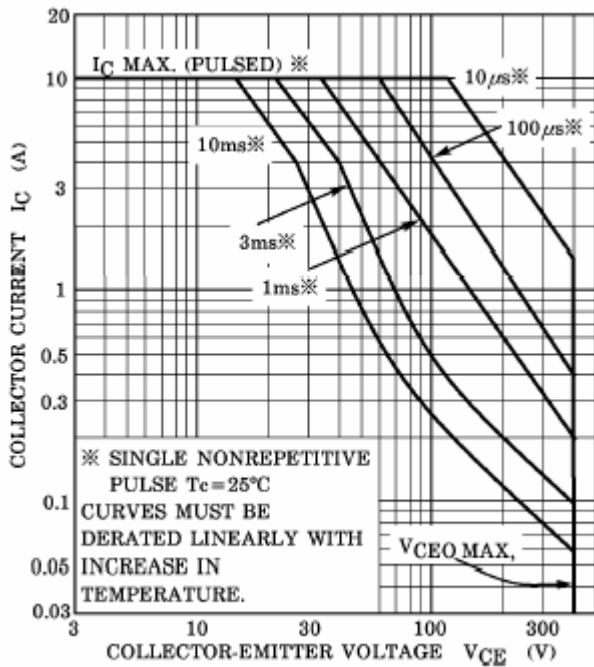


Fig.7 Safe Operating Area